

ABSTRACT

HIGHLY HEAT-RESISTANT PLASMA ETCHING ELECTRODE AND DRY ETCHING DEVICE INCLUDING THE SAME

It is an object of the present invention to provide a plasma etching electrode which is prevented from being contaminated with an impurity, secures good thermal and electrical conductance and heat resistance at the joint between the electrode plate and pedestal (or supporting ring), and hence improves the etching characteristics and silicon wafer yield. It is another object to provide the dry etching device including the same.

The present invention provides a highly heat-resistant plasma etching electrode, comprising an electrode plate of silicon supported by and fast, uniformly joined to a pedestal by an adhesive agent, wherein (a) the pedestal is made of graphite, and (b) an epoxy resin containing polycarbodiimide resin and carbon powder are used for the adhesive agent, and also provides the dry etching device including the same.

(Figure 1)

